

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-30V	10mΩ @ V _{GS} = -10V	-11.5A
	18mΩ @ V _{GS} = -4.5V	-8.7A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

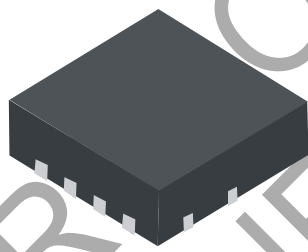
- Low R_{DS(ON)} – Ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMP3017SFGQ](#))**

Mechanical Data

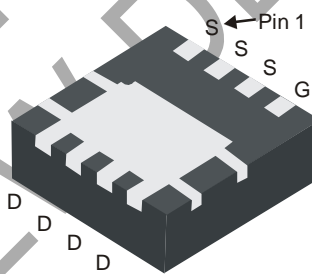
- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)



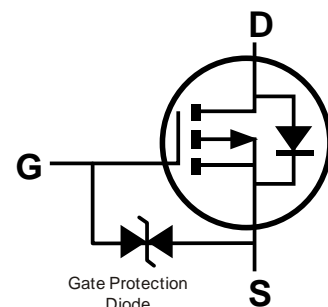
ESD PROTECTED



Top View



Bottom View



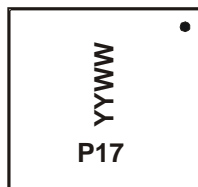
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3017SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMP3017SFG-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



P17 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-11.5 -9.4	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-15.2 -12.1	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	-3.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-80	A
Avalanche Current (Note 7) L = 1mH			I _{AR}	-14	A
Repetitive Avalanche Energy (Note 7) L = 1mH			E _{AR}	104	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.94	W
	T _A = +70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	137	°C/W
	t < 10s		82	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.2	W
	T _A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	60	°C/W
	t < 10s		36	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	3.0	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8.5	10	mΩ	V _{GS} = -10V, I _D = -11.5A
		—	15	18		V _{GS} = -4.5V, I _D = -8.5A
Forward Transfer Admittance	Y _{fs}	—	24	—	S	V _{DS} = -5V, I _D = -11.5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2246	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	352	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	294	—	pF	
Gate Resistance	R _g	—	5.1	12	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -5V)	Q _g	—	20.5	—	nC	V _{DS} = -15V, I _D = -11.5A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	41	—	nC	
Gate-Source Charge	Q _{gs}	—	7.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	8.0	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	7.5	—	ns	V _{DD} = -15V, V _{GS} = -10V, R _G = 6Ω, I _D = -11.5A
Turn-On Rise Time	t _R	—	15.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	45.6	—	ns	
Turn-Off Fall Time	t _F	—	36.8	—	ns	
BODY DIODE CHARACTERISTICS						
Diode Forward Voltage	V _{SD}	—	-0.7	—	V	V _{GS} = 0V, I _S = -1A
Reverse Recovery Time (Note 9)	t _{RR}	—	20	—	ns	I _S = -11.5A, dI/dt = 100A/μs
Reverse Recovery Charge (Note 9)	Q _{RR}	—	9.5	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

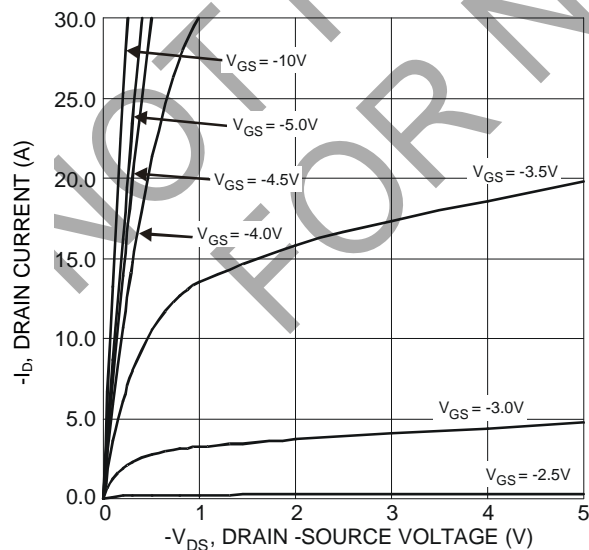


Figure 1 Typical Output Characteristics

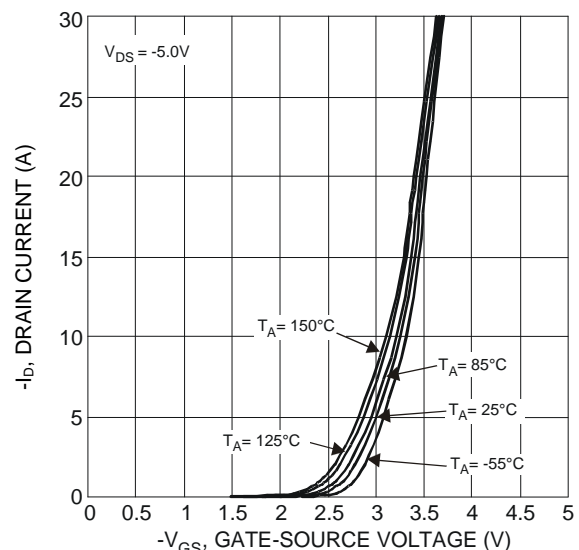


Figure 2 Typical Transfer Characteristics

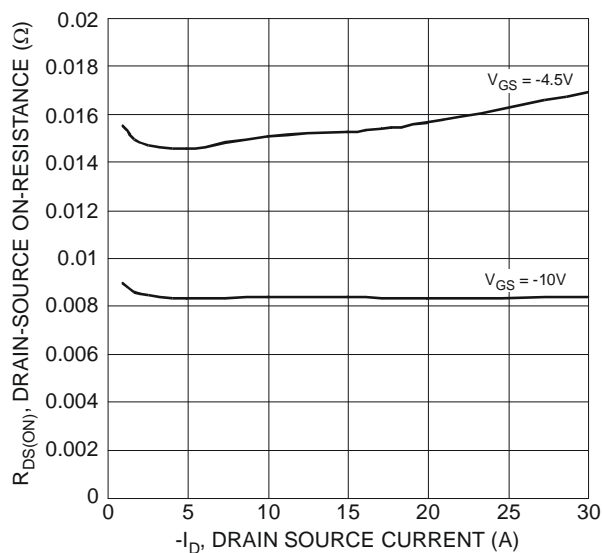


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

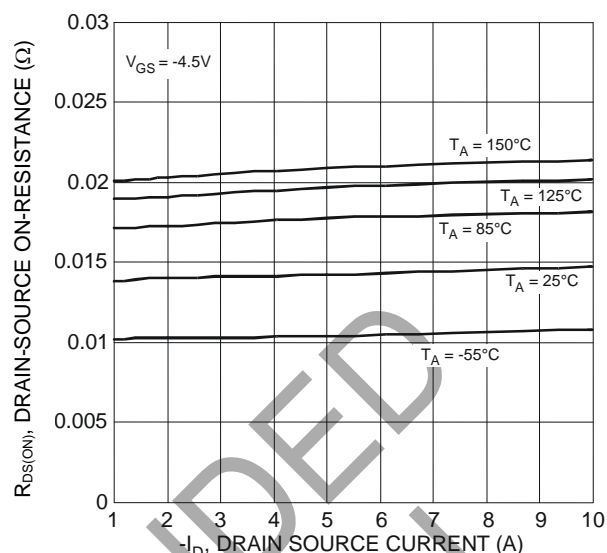


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

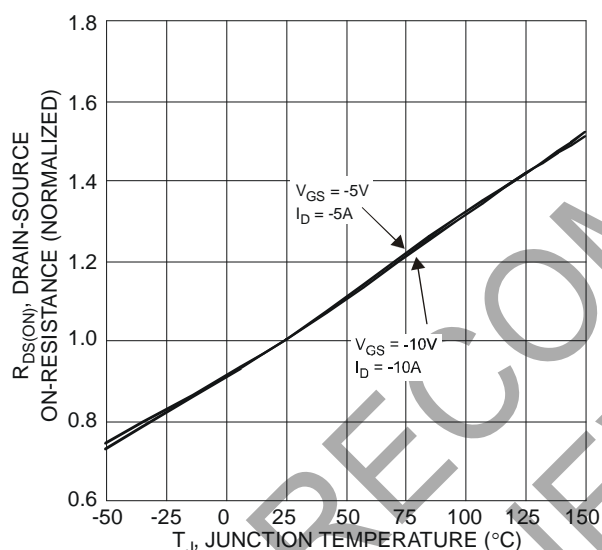


Figure 5 On-Resistance Variation with Temperature

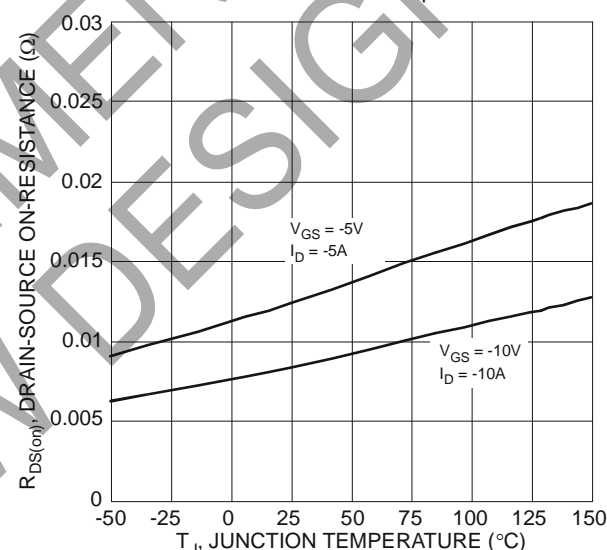


Figure 6 On-Resistance Variation with Temperature

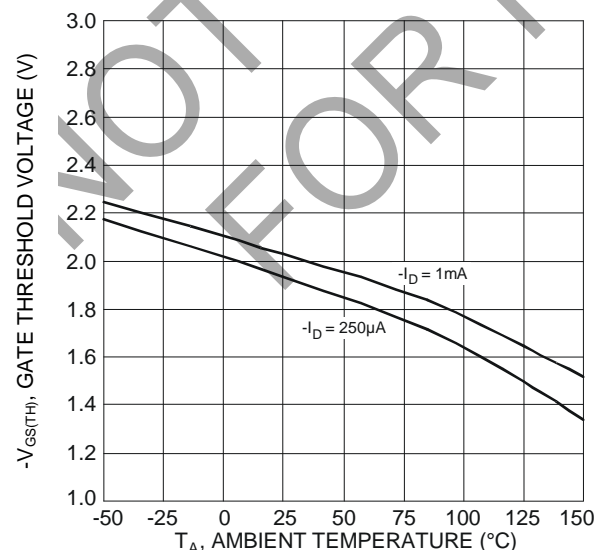


Figure 7 Gate Threshold Variation vs. Ambient Temperature

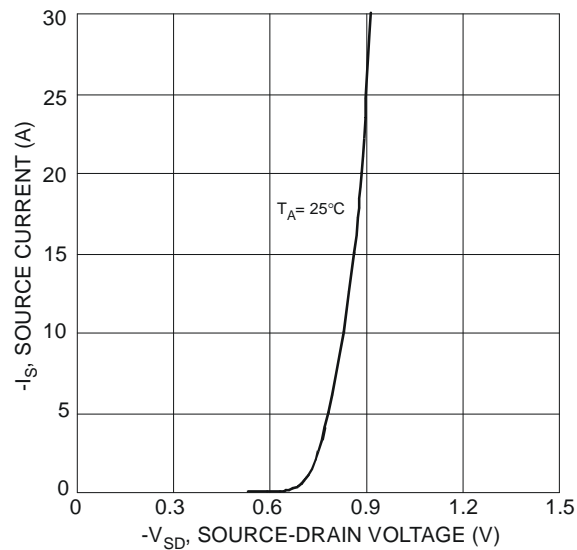
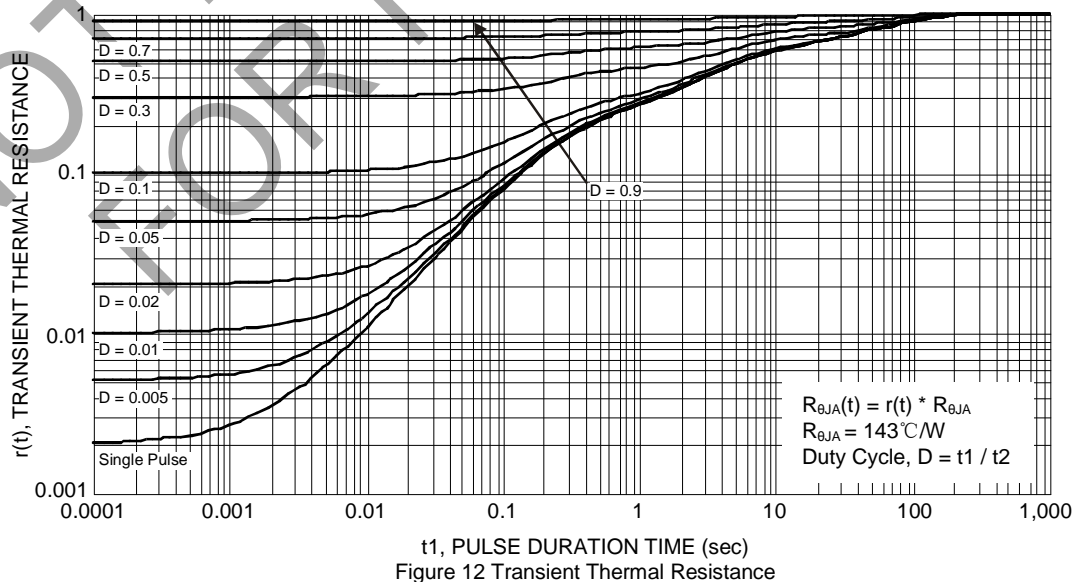
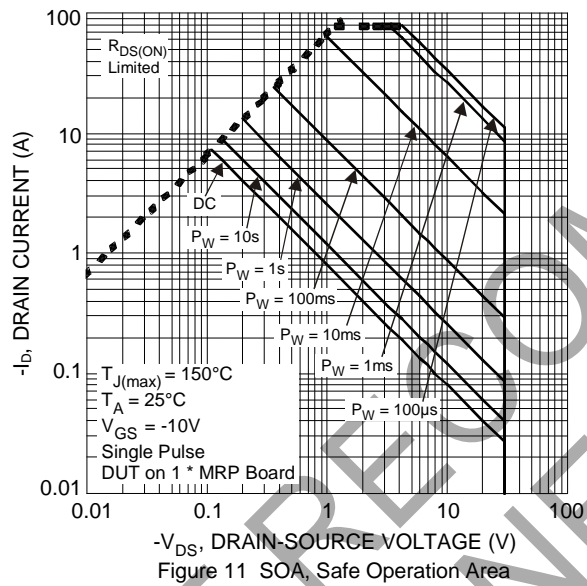
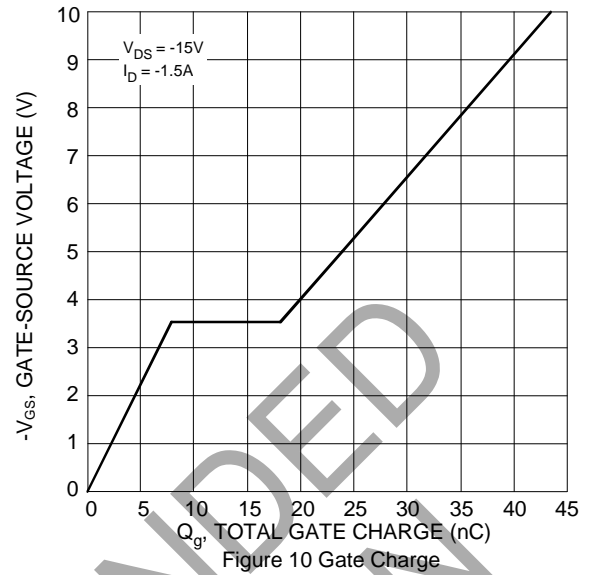
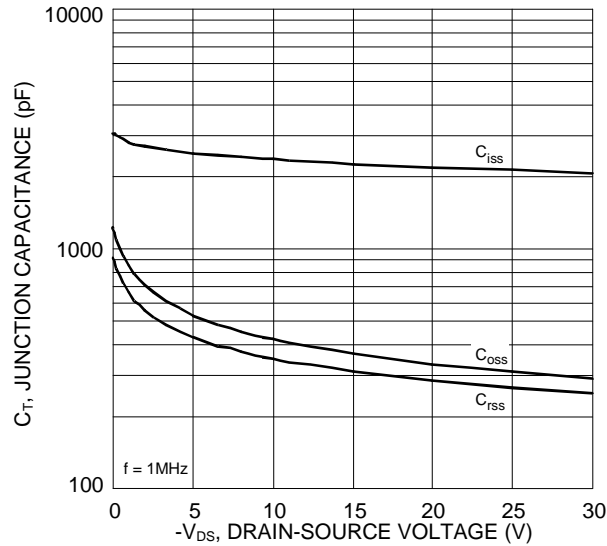
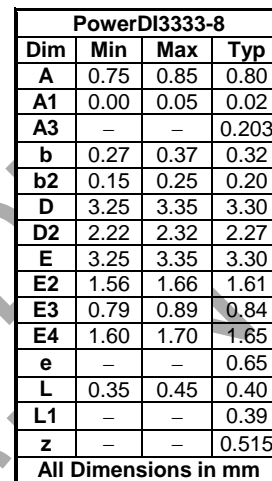


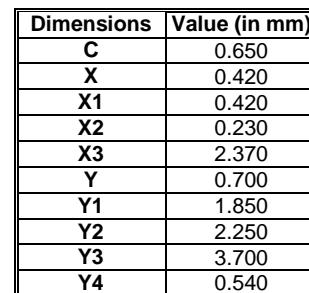
Figure 8 Diode Forward Voltage vs. Current



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